GIET MAIN CAMPUS AUTONOMOUS, GUNUPUR - 765022									
Registration No:									M.TECH
	SEMESTER I WER SEMICO	ONDUCTO	OR DEVI	CES &	& M0	ODE		BER 201	8
ime: 3 Hours Branch: PE, Subject Code: MPEPE1043 (Regulations 2018) Max Marks : 70 PART-A (10 X 2=20 Marks) Question Code:RD1									RD18002074
 Answer the following What are converter Brief the phenome Differentiate betw What are the parameter devices. Differentiate betw What is the need of Define the concept Define SOA. What are the avail List out the advant 	r grade and inve enon of seconda een GTO & TR neters that affect een NPN and P of isolation for p t of latching. able ratings of v	ry breakdow IAC. ct the life tin NP transisto power semic warious pow	wn in BJT me and pe ors. conductor	S. Serform device	es.	-		emicondu	ctor
	PART- Answer any fiv	B (5 X 10= e questions		,	ving.				
2. a. What are the advantages and disadvantages of power semiconductor devices?b. Briefly explain the power handling capability of various devices.							[5] [5]		
3. a. With the help of neat sketch, explain the electrical equivalent circuit of thermal model of a power device.b. Explain the necessity of using isolation, pulse transformer as protection circuits								a [5]	
4. a. Explain the switching characteristics of thyristors during turn-on and turn-offb. Draw and explain the static and switching characteristics of power MOSFET.								[5] [5]	
5. a. Draw and explain the static and switching characteristics of Thyristorb. Compare FCT, RCT and IGCT								[5] [5]	
6. a. Explain the Forward, Reverse and switching characteristics of power diodeb. Explain the Power handling capability and Safe operating Area of Power device								[5] [5]	
7. a. Explain the basic structure and operating characteristics of an MCT.b. Explain the basic structure and operating of an IGBT									[5] [5]
8. a. Draw and explain the b. Explain the design of	•								[5] [5]